

**1N70-CB**

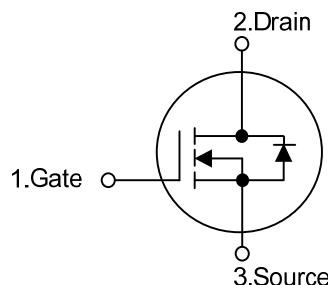
Preliminary

**Power MOSFET****1.0A, 700V N-CHANNEL  
POWER MOSFET****■ DESCRIPTION**

The UTC **1N70-CB** is a high voltage MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

**■ FEATURES**

- \*  $R_{DS(ON)} < 12\Omega$  @  $V_{GS} = 10V$ ,  $I_D = 0.5A$
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness

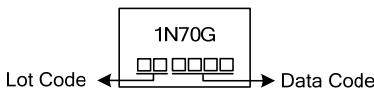
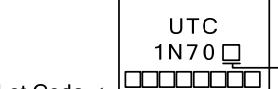
**■ SYMBOL****■ ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
-	1N70G-AA3-R	SOT-223	G	D	S	Tape Reel
1N70L-TA3-T	1N70G-TA3-T	TO-220	G	D	S	Tube
1N70L-TF1-T	1N70G-TF1-T	TO-220F1	G	D	S	Tube
1N70L-TF2-T	1N70G-TF2-T	TO-220F2	G	D	S	Tube
1N70L-TF3-T	1N70G-TF3-T	TO-220F	G	D	S	Tube
1N70L-TM3-T	1N70G-TM3-T	TO-251	G	D	S	Tube
1N70L-TN3-R	1N70G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1) T: Tube, R: Tape Reel		
	(2) AA3: SOT-223, TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TN3: TO-252		
	(3) L: Lead Free, G: Halogen Free and Lead Free		

**■ MARKING**

SOT-223	TO-220 / TO-220F / TO-220F1 TO-220F2 / TO-251 / TO-252
 Lot Code ← 1 → Data Code	 Lot Code ← 1 → Data Code L: Lead Free G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	700	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	1.0	A
	Pulsed (Note 2)	$I_{DM}$	4.0	A
Avalanche Current (Note 2)		$I_{AR}$	1.5	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	11	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.6	V/ns
Power Dissipation	SOT-223	$P_D$	9	W
	TO-220		40	W
	TO-220F/TO-220F1		21	W
	TO-220F2		28	W
	TO-251/TO-252			
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L=10\text{mH}$ ,  $I_{AS}=1.5\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 1.0\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	SOT-223	$\theta_{JA}$	150	$^\circ\text{C/W}$
	TO-220/TO-220F		62.5	$^\circ\text{C/W}$
	TO-220F1/TO-220F2		110	$^\circ\text{C/W}$
Junction to Case	TO-251/TO-252	$\theta_{JC}$	14	$^\circ\text{C/W}$
	SOT-223		3.13	$^\circ\text{C/W}$
	TO-220		5.95	$^\circ\text{C/W}$
	TO-220F/TO-220F1		4.46	$^\circ\text{C/W}$
	TO-220F2			
	TO-251/TO-252			

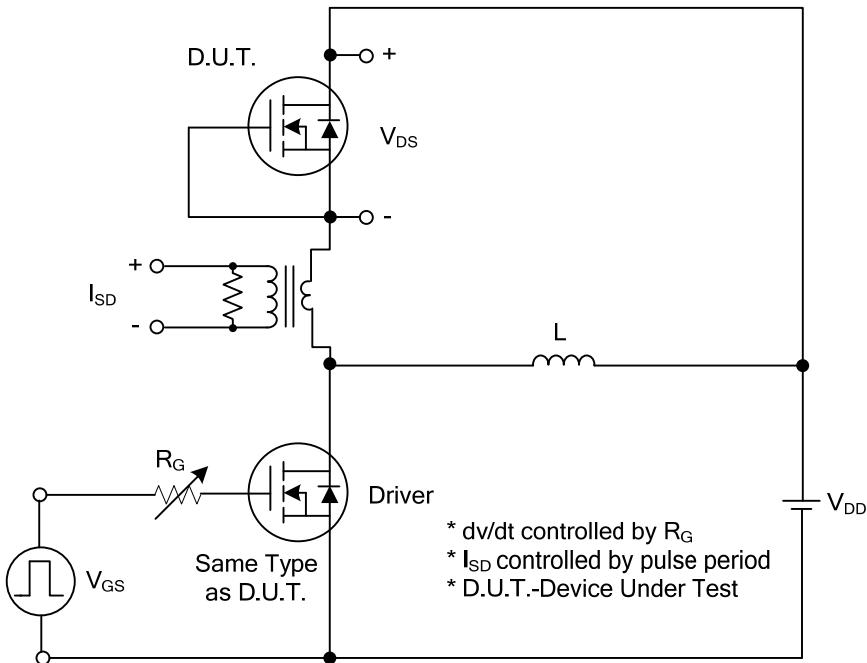
■ ELECTRICAL CHARACTERISTICS ( $T_J=25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	700			V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}} = 700\text{V}, V_{\text{GS}} = 0\text{V}$		1		$\mu\text{A}$
Gate-Source Leakage Current	Forward	$V_{\text{GS}} = 30\text{V}, V_{\text{DS}} = 0\text{V}$		100		nA
	Reverse	$V_{\text{GS}} = -30\text{V}, V_{\text{DS}} = 0\text{V}$		-100		nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{\text{GS(TH)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 0.5\text{A}$		12		$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{\text{ISS}}$	$V_{\text{DS}} = 25\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		195		pF
Output Capacitance	$C_{\text{OSS}}$			29		pF
Reverse Transfer Capacitance	$C_{\text{RSS}}$			15		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge (Note 1)	$Q_G$	$V_{\text{DS}} = 50\text{V}, V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 0.83\text{A}$ $I_G = 100\mu\text{A}$ (Note 1, 2)		18		nC
Gate to Source Charge	$Q_{\text{GS}}$			1.7		nC
Gate to Drain Charge	$Q_{\text{GD}}$			1.7		nC
Turn-ON Delay Time (Note 1)	$t_{\text{D(ON)}}$	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 10\text{V}, I_{\text{D}} = 0.5\text{A}$ , $R_G = 25\Omega$ (Note 1, 2)		36		ns
Rise Time	$t_R$			14		ns
Turn-OFF Delay Time	$t_{\text{D(OFF)}}$			78		ns
Fall-Time	$t_F$			12		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	$I_{\text{SD}}$				1.0	A
Maximum Body-Diode Pulsed Current	$I_{\text{SM}}$				4.0	A
Drain-Source Diode Forward Voltage (Note 1)	$V_{\text{SD}}$	$I_S = 1.0\text{A}, V_{\text{GS}} = 0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	$t_{\text{rr}}$	$I_S = 1.0\text{A}, V_{\text{GS}} = 0\text{V}$ , $dI_F/dt = 100\text{A}/\mu\text{s}$		250		nS
Body Diode Reverse Recovery Charge	$Q_{\text{rr}}$			0.43		$\mu\text{C}$

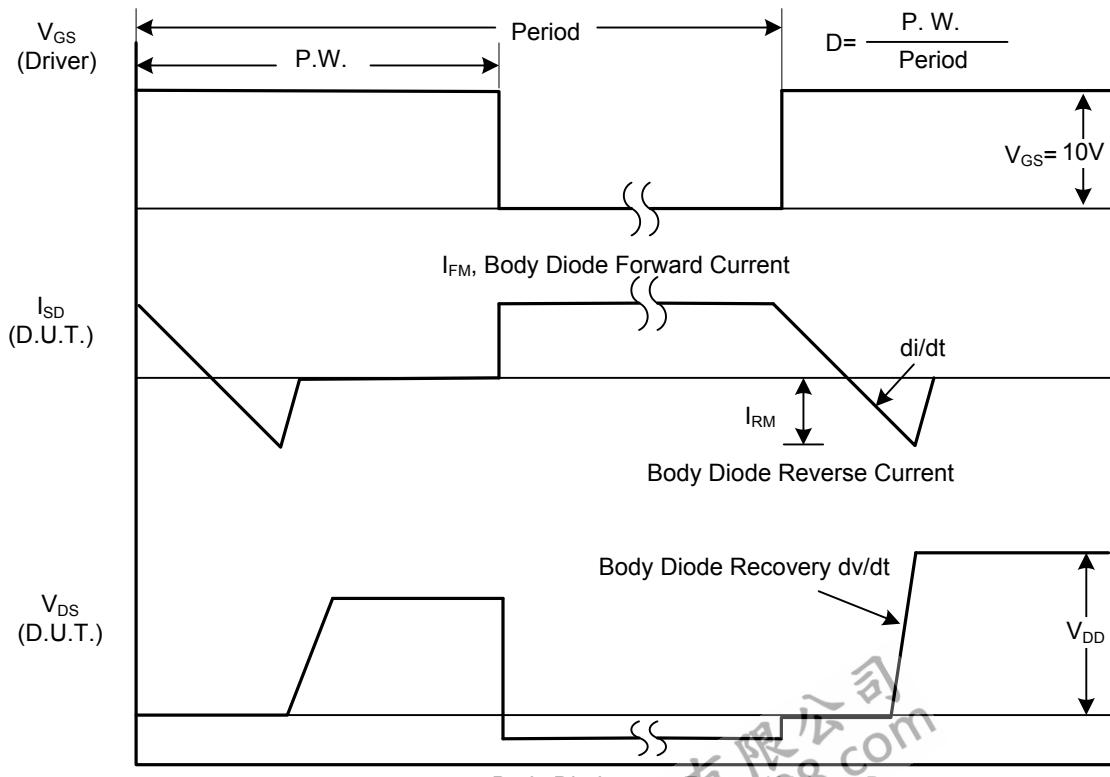
Notes: 1. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

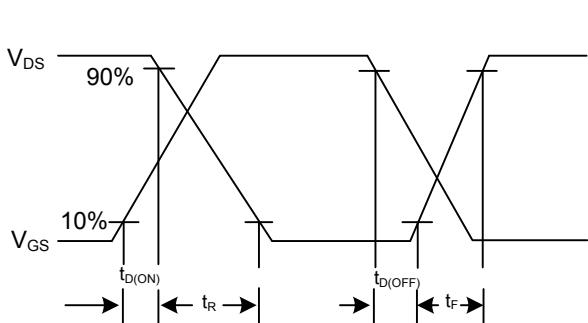
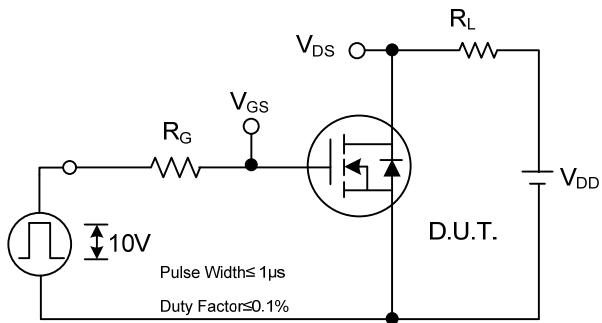


**Peak Diode Recovery dv/dt Test Circuit**



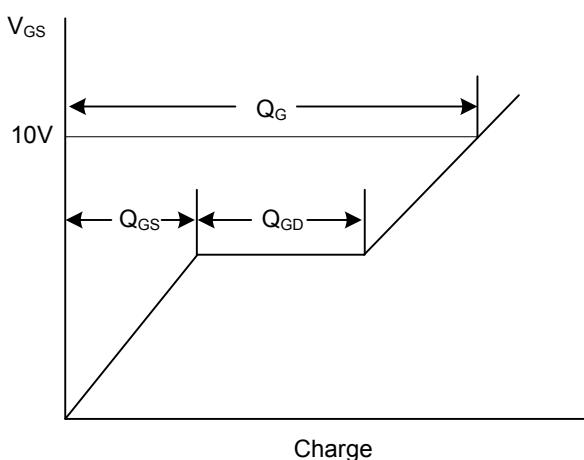
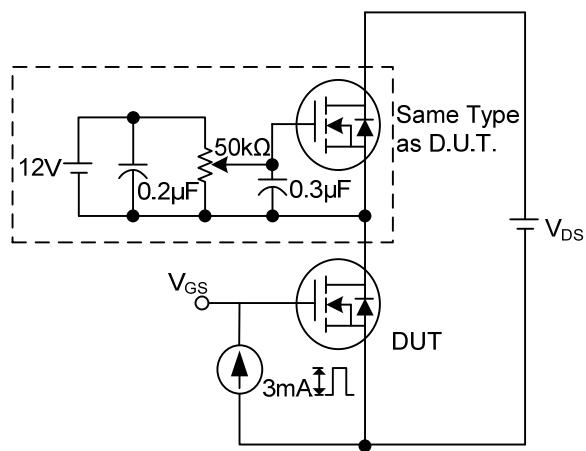
**Peak Diode Recovery dv/dt Waveforms**

## ■ TEST CIRCUITS AND WAVEFORMS (Cont.)



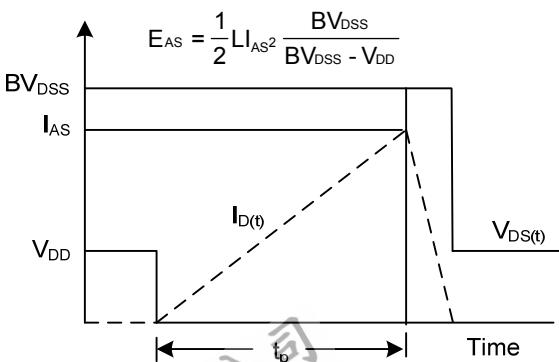
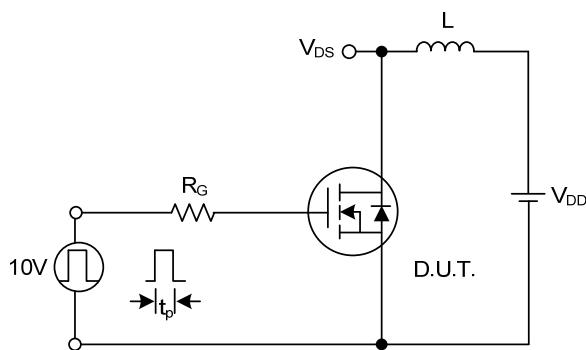
Switching Test Circuit

Switching Waveforms



Gate Charge Test Circuit

Gate Charge Waveform



Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

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